

# Superconducting Properties of $\text{MgCNi}_3$ Films

D. P. Young, M. M. Moldovan, D. D. Craig, and P. W. Adams

Department of Physics and Astronomy

Louisiana State University

Baton Rouge, Louisiana, 70803

Julia Y. Chan

Department of Chemistry

Louisiana State University

Baton Rouge, LA, 70803

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We report the magnetotransport properties of thin polycrystalline films of the recently discovered non-oxide perovskite superconductor  $\text{MgCNi}_3$ .  $\text{CNi}_3$  precursor films were deposited onto sapphire substrates and subsequently exposed to Mg vapor at 700 °C. We report transition temperatures ( $T_c$ ) and critical field values ( $H_{c2}$ ) of  $\text{MgCNi}_3$  films ranging in thickness from 7.5 nm to 100 nm. Films thicker than 40 nm have a  $T_c \approx 8$  K, and an upper critical field  $H_{c2}(T = 0) = 14$  T, which are both comparable to that of polycrystalline powders. Hall measurements in the normal state give a carrier density,  $n = 4.2 \times 10^{22} \text{ cm}^{-3}$ , that is approximately 4 times that reported for bulk samples.

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Over the last decade a broad and significant research effort has emerged aimed at identifying and characterizing relatively low- $T_c$  superconductors that are exotic in their normal state properties and/or order parameter symmetries. Examples include the ternary borocarbides  $\text{LnNi}_2\text{B}_2\text{C}$ , where Ln is a lanthanide element [1], the non-copper layered perovskite  $\text{Sr}_2\text{RuO}_4$  [2], and the superconducting itinerant ferromagnets  $\text{UGe}_2$  [3] and  $\text{ZrZn}_2$  [4]. The recently discovered intermetallic  $\text{MgCNi}_3$  [5] falls into this class in that its major constituent, Ni, is ferromagnetic, generating speculation that the system may be near a ferromagnetic ground state [6]. In addition,  $\text{MgCNi}_3$  is the only known non-oxide perovskite that superconducts, and is thus a compelling analog to the high- $T_c$  perovskites. Notwithstanding the widespread interest in  $\text{MgCNi}_3$ , its status as a non-BCS superconductor remains controversial [7, 8]. Electron tunneling studies of the density of states in polycrystalline powders have yielded conflicting results as to whether or not  $\text{MgCNi}_3$  exhibits a BCS density of states spectrum [9, 10]. Tunneling into sintered powders is technically difficult, and indeed, a detailed quantitative characterization of  $\text{MgCNi}_3$  has, in part, been hampered by the fact that only polycrystalline powder samples have been available. Obviously, single crystal samples and/or polycrystalline films would be a welcome development both in terms of fundamental research and possible applications. In the present Communication we present magnetotransport studies of thin  $\text{MgCNi}_3$  films. We show that the transition temperature of the films is only weakly dependent upon film thickness for thicknesses greater than 10 nm, and that both the transition temperature and critical field values of films with thicknesses greater than 40 nm are comparable to that of powder samples synthesized via standard solid state reaction processes.

The  $\text{MgCNi}_3$  films were grown by first depositing thin films of the metastable intermetallic  $\text{CNi}_3$  onto sapphire substrates by electron-beam evaporation of  $\text{CNi}_3$  targets. Typical deposition rates were 0.1 nm/s in a  $2 \times 10^{-6}$  Torr vacuum. All of the evaporations were made at room temperature, and the resulting films were handled in air. The targets consisted of arc-melted buttons of high purity graphite (Johnson Matthey, 99.999%) and nickel (Johnson Matthey, 99.999%). The buttons were made with a starting stoichiometry of  $\text{CNi}_{3.25}$  to compensate for some loss of nickel during the melting process. The  $\text{CNi}_3$  structure of the pristine film was verified by x-ray diffraction. Scanning electron microscopy showed the  $\text{CNi}_3$  film to be very smooth with no discernible morphological features in  $10 \mu\text{m} \times 10 \mu\text{m}$  micrographs. The films were also quite adherent, and could not be pulled off with Scotch tape.

$\text{MgCNi}_3$  was synthesized by first sealing pristine  $\text{CNi}_3$  films in a quartz tube under vacuum with approximately 0.1 g of magnesium metal (Alfa Aesar, 99.98%). The tube was then placed in a furnace at 700 °C for 20 minutes, after which the entire tube was quenched-cooled to room temperature. X-ray powder diffraction analysis of the magnesiumated films verified that  $\text{MgCNi}_3$  was formed. Intensity data were collected using a Bruker Advance D8 powder diffractometer at ambient temperature in the  $2\theta$  range between 20 deg and 60 deg with a step width of 0.02 deg and a 6 s count time. The inset of Fig. 1 shows the X-ray diffraction data for a 90 nm film on a sapphire substrate. The powder pattern shows that the film has good crystallinity and that it can be indexed according to the  $\text{Pm}\bar{3}\text{m}$  space group, with  $a = 0.38070(2) \text{ nm}$ . The pattern also indicates that the films grew preferentially along the  $(h00)$  reflections. Electrical resistivity measurements were made by the standard 4-probe AC technique at 27 Hz with an excitation current of 0.01 mA. Two 0.1 mm diameter platinum wires were attached to the films with silver epoxy, and the measurements were

performed in a 9-Tesla Quantum Design PPM S system from 1.8 – 300 K.

In the main panel of Fig. 1 we plot the resistivity of a 7.5 nm and a 60 nm  $\text{In}$  as function of temperature in zero magnetic field. The thickness values refer to that of the  $\text{CNi}_3$  layers as determined by a quartz crystal deposition monitor. Subsequent probe measurements of the magnetized  $\text{In}$ s did not show any significant increase in  $\text{In}$  thickness. We note that the resistance ratio,  $\rho_{290\text{K}}/\rho_{10\text{K}}$  of the 60 nm  $\text{In}$ , is slightly better than that reported for pressed pellet samples [5, 11]. Indeed, the overall shape of the 60 nm curve is very similar to that of  $\text{MgCNi}_3$  powders, but the normal state resistivity  $\rho_{10\text{K}} \approx 20 \text{ m}\Omega$ , is a factor of 2-6 lower than polycrystalline powder values. The midpoint of the resistive transitions in Fig. 1 are 8.2 K and 3.9 K for the 60 nm and 7.5 nm  $\text{In}$ s, respectively. In Fig. 2 we plot the resistive transitions for a variety of  $\text{In}$  thicknesses,  $d$ . Note that the transition temperature  $T_c$  is relatively insensitive to  $d$  down to about  $d = 15 \text{ nm}$ , below which  $T_c$  is suppressed and broadened.

The perpendicular critical field behavior of a 60 nm  $\text{In}$  is shown in Fig. 3. As is the case with pressed pellets of  $\text{MgCNi}_3$  powder, the resistive critical field transition width is only weakly temperature dependent [11]. We define the critical field,  $H_{c2}$ , as the midpoint of the transitions in Fig. 3, and in Fig. 4 we plot critical values as a function of temperature. The solid symbols represent a 60 nm  $\text{In}$ , and the open symbols are for a polycrystalline sample from Ref. 11. Clearly the 60 nm critical field behavior is almost identical to that of sintered  $\text{MgCNi}_3$  powders, which are known to have an anomalously high critical field and excellent flux pinning properties [12]. Future studies of the critical current behavior of the  $\text{In}$ s should prove interesting.

We have also made Hall measurements of the  $\text{In}$ s in the normal state between 10 K and room temperature. In the inset of Fig. 4 we show the Hall voltage as a function of magnetic field at 10 K and 200 K. The solid lines are linear fits to the data. The slopes of the lines are proportional to the Hall coefficient  $R_H = 1/en$ , where  $n$  is the effective carrier density. Clearly the  $\text{MgCNi}_3$   $\text{In}$ s have electron-like carriers as is the case in the bulk material. However, the calculated carrier density at 10 K,  $n = 4.2 \times 10^{22} \text{ cm}^{-3}$ , is about 4 times larger than that reported in Ref. 11 for sintered powder samples. If, indeed, the carrier density of the  $\text{In}$ s is enhanced over the bulk values, then it is somewhat surprising that the superconducting properties remain essentially unchanged relative to that of the bulk material.

In conclusion, we report the first synthesis of  $\text{MgCNi}_3$   $\text{In}$ s and find that their transition temperatures and critical field behavior are very similar to that of bulk powder samples. The  $\text{In}$ s are smooth, adherent, and show no significant air sensitivity. A thin  $\text{In}$  geometry lends itself quite well to planar counter-electrode tunnelling measurements of the electronic density states, thus providing a compelling alternative to scanning electron microscopy tunneling. Such a study in  $\text{MgCNi}_3$   $\text{In}$ s should prove invaluable in resolving the nature of the superconducting condensate. The  $\text{In}$  geometry will also allow access to the spin paramagnetic limit in parallel magnetic field studies, as well as possible electric field modulation of the carrier density via gating.

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## Figures

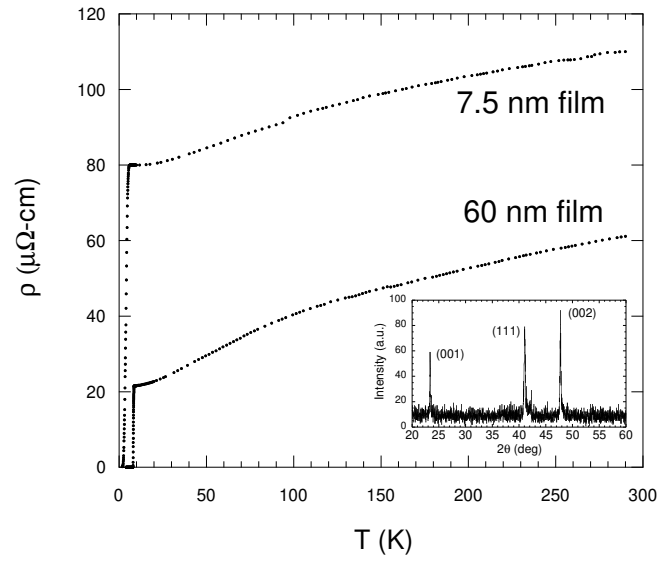


FIG. 1: Resistivity of a 60 nm and a 7.5 nm  $\text{MgCNi}_3$  film as a function of temperature in zero magnetic field. The midpoint transition temperatures of the 60 nm and 7.5 nm films were  $T_c = 8.2$  K and  $T_c = 3.9$  K, respectively. Inset: X-ray powder diffraction pattern of a 90 nm  $\text{MgCNi}_3$  film on sapphire.

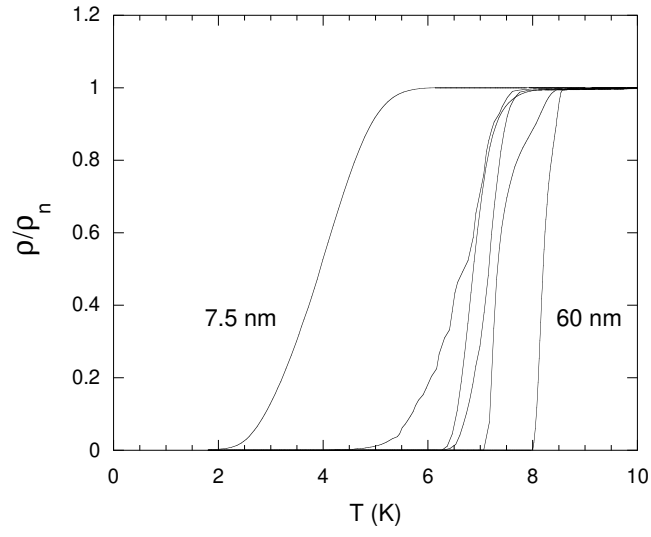


FIG. 2: Resistive transitions for varying  $t_n$  thickness. The curves correspond from left to right to  $\text{MgCNi}_2$  layer thicknesses of 7.5 nm, 15 nm, 30 nm, 45 nm, and 60 nm.

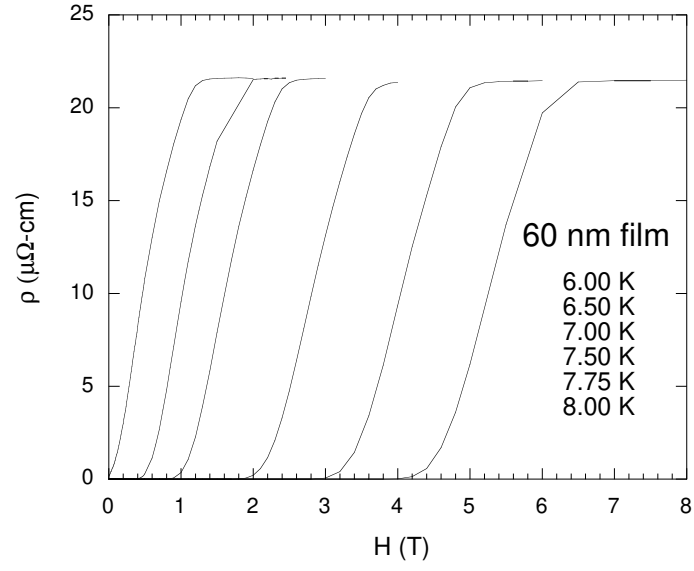


FIG. 3: Resistive critical field transitions of a 60 nm  $\text{In}$  at different temperatures. The magnetic field was applied perpendicular to the  $\text{In}$  surface.

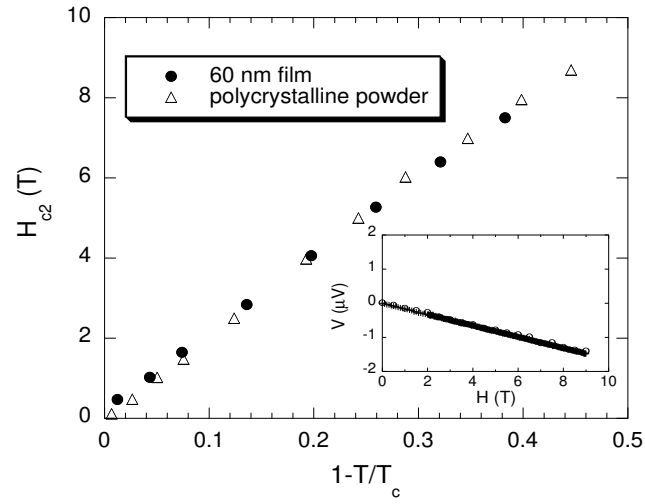


FIG. 4: Upper critical field values of the 60 nm film of Fig. 3 (solid symbols) and a polycrystalline sample (open symbols) as a function of reduced temperature. Inset: Hall voltage of a 90 nm  $\text{MgCNi}_2$  film using a 0.1 mA probe current at 10 K (crosses) and 200 K (circles). The solid lines are linear least-squares fits to the data. The low temperature data corresponds to a carrier density of  $n = 4.2 \times 10^{22} \text{ cm}^{-3}$ .